





60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(on)} Max | I _D Max T _A = +25°C (Note 6) |
|----------------------|---------------------------------|--|
| -60V | $125m\Omega$ @ $V_{GS} = -10V$ | -3.0 A |
| -60 V | 190mΩ @ V _{GS} = -4.5V | -2.4 A |

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

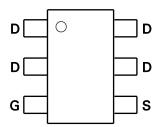
- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

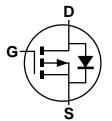
- Case: SOT-26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208
- Weight: 0.018 grams (Approximate)







Pin Out - Top View



Equivalent Circuit

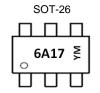
Ordering Information (Note 4)

| Part Number | Compliance | Case | Quantity per reel | | |
|--------------|------------|--------|-------------------|--|--|
| ZXMP6A17E6TA | Standard | SOT-26 | 3,000 | | |

Note:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



6A17 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2015 | 2016 | 2017 | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | С | D | E | F | G | Н | I | J | K | L | М | N |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| | Characteristic | | Symbol | Value | Unit |
|--|-----------------|---------------------------------------|------------------|-------|------|
| Drain-Source Voltage | | | V _{DSS} | -60 | V |
| Gate-Source Voltage | | | V _{GS} | ±20 | V |
| - | | (Note 6) | | -3 | |
| Continuous Drain Current | $V_{GS} = -10V$ | $T_A = +70^{\circ}C \text{ (Note 6)}$ | I_{D} | -2.4 | Α |
| | | (Note 5) | | -2.3 | |
| Pulsed Drain Current | $V_{GS} = -10V$ | (Note 7) | I _{DM} | -13.6 | Α |
| Continuous Source Current (Body Diode) | | (Note 6) | Is | -2.5 | Α |
| Pulsed Source Current (Bod | y Diode) | (Note 7) | I _{SM} | -13.6 | Α |

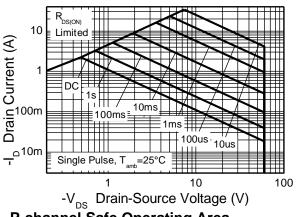
Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|----------|-----------------------------------|--------------|-------|--|
| Power Dissipation | (Note 5) | | 1.1 8.8 | W | |
| Linear Derating Factor | (Note 6) | P _D | 1.92 15.4 | mW/°C | |
| Thermal Resistance, Junction to Ambient | (Note 5) | В | 113 | °C/W | |
| mermai Resistance, Junction to Ambient | (Note 6) | − R _{θJA} | 65 | C/VV | |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C | |

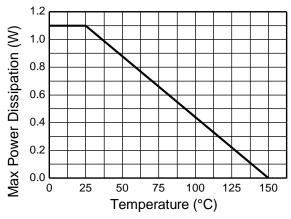
Notes:

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at $t \le 5$ sec.
- 7. Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

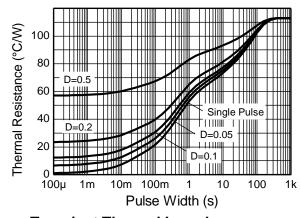
Thermal Characteristics



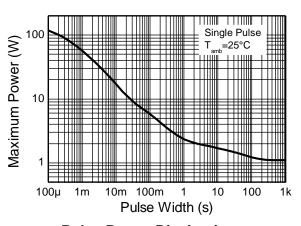
P-channel Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

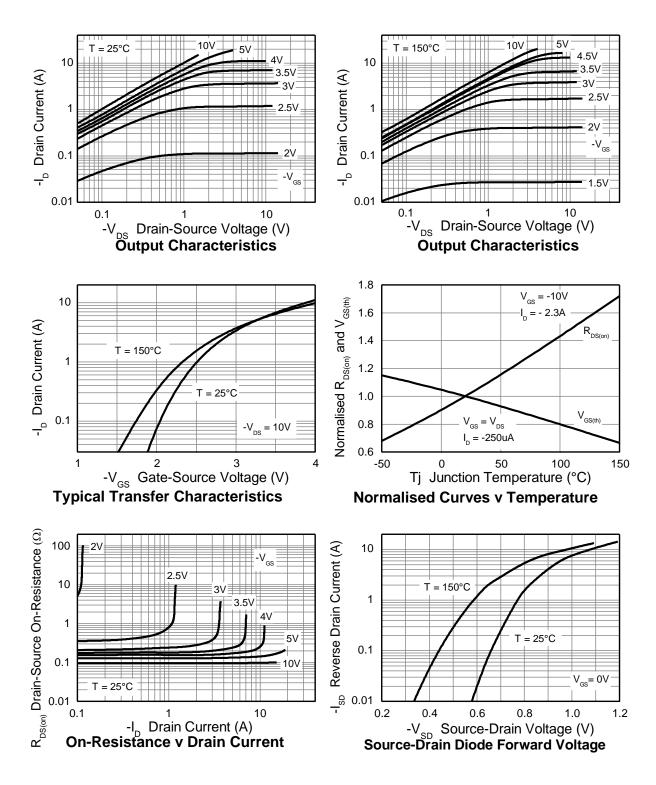
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|----------------------|-----|-------|-------|------|--|--|
| OFF CHARACTERISTICS | | | | | | · | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -60 | _ | _ | V | $I_D = -250 \mu A$, $V_{GS} = 0 V$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | -1 | μΑ | $V_{DS} = -60V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS | | | | | | · | |
| Gate Threshold Voltage | $V_{GS(th)}$ | -1 | _ | -3 | V | $I_D = -250 \mu A, V_{DS} = V_{GS}$ | |
| Static Drain Source On Registence (Note 9) | | | 0.100 | 0.125 | Ω | $V_{GS} = -10V, I_D = -2.3A$ | |
| Static Drain-Source On-Resistance (Note 8) | R _{DS} (ON) | _ | 0.130 | 0.190 | 12 | $V_{GS} = -4.5V, I_D = -1.9A$ | |
| Forward Transconductance (Notes 8 & 9) | g fs | _ | 4.7 | _ | S | $V_{DS} = -15V, I_{D} = -2.3A$ | |
| Diode Forward Voltage (Note 8) | V_{SD} | _ | -0.85 | -0.95 | V | $I_S = -2A$, $V_{GS} = 0V$ | |
| Reverse Recovery Time (Note 9) | t _{rr} | | 25.1 | _ | ns | 1 170 di/dt 1000/up | |
| Reverse Recovery Charge (Note 9) | Qrr | _ | 27.2 | _ | nC | I _F = -1.7A, di/dt = 100A/μs | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | |
| Input Capacitance | C _{iss} | _ | 637 | _ | pF | 1/ 201/ 1/ 01/ | |
| Output Capacitance | Coss | _ | 70 | _ | pF | $V_{DS} = -30V, V_{GS} = 0V$ - f = 1MHz | |
| Reverse Transfer Capacitance | C_{rss} | | 53 | _ | рF | 1 – 11011 12 | |
| Total Gate Charge (Note 10) | Qg | _ | 9.8 | _ | nC | $V_{GS} = -5V$ | |
| Total Gate Charge (Note 10) | Q_{g} | _ | 17.7 | _ | nC | V _{DS} = -30V | |
| Gate-Source Charge (Note 10) | Q_{gs} | _ | 1.6 | _ | nC | $V_{GS} = -10V$ $I_{D} = -2.3A$ | |
| Gate-Drain Charge (Note 10) | Q_{gd} | _ | 4.4 | _ | nC | | |
| Turn-On Delay Time (Note 10) | t _{D(on)} | _ | 2.6 | _ | ns | | |
| Turn-On Rise Time (Note 10) | t _r | _ | 3.4 | _ | ns | $V_{DD} = -30V, V_{GS} = -10V$ | |
| Turn-Off Delay Time (Note 10) | t _{D(off)} | _ | 26.2 | _ | ns | $I_D = -1A, R_G \cong 6\Omega$ | |
| Turn-Off Fall Time (Note 10) | t _f | | 11.3 | _ | ns | 7 | |

Notes:

^{8.} Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
9. For design aid only, not subject to production testing.
10. Switching characteristics are independent of operating junction temperatures.

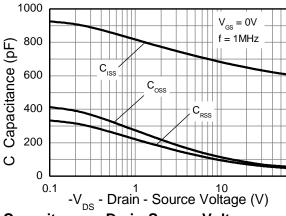


Typical Characteristics

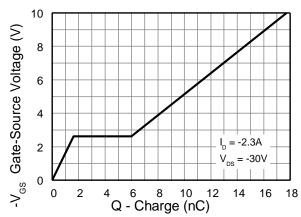




Typical Characteristics (cont.)

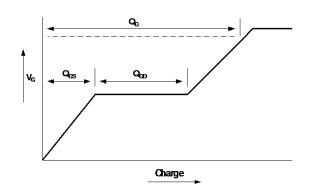


Capacitance v Drain-Source Voltage

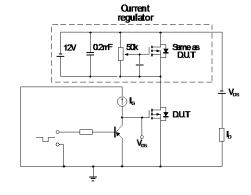


Gate-Source Voltage v Gate Charge

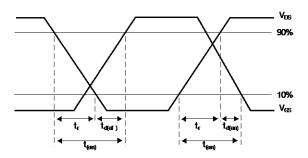
Test Circuits



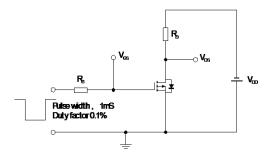
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

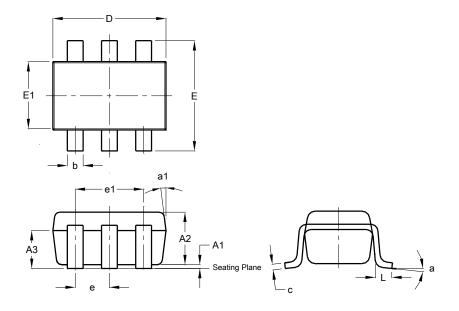


Switching time test circuit



Package Outline Dimensions

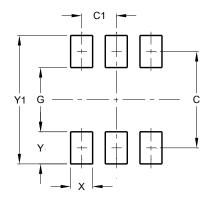
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| | SOT26 | | | | | | | |
|------|---------------|-------|-------|--|--|--|--|--|
| Dim | Min | Max | Тур | | | | | |
| A1 | 0.013 | 0.10 | 0.05 | | | | | |
| A2 | 1.00 | 1.30 | 1.10 | | | | | |
| A3 | 0.70 | 0.80 | 0.75 | | | | | |
| b | 0.35 | 0.50 | 0.38 | | | | | |
| С | 0.10 | 0.20 | 0.15 | | | | | |
| D | D 2.90 | | 3.00 | | | | | |
| е | - | - | 0.95 | | | | | |
| e1 - | | - | 1.90 | | | | | |
| E | 2.70 | 3.00 | 2.80 | | | | | |
| E1 | 1.50 | 1.70 | 1.60 | | | | | |
| L | L 0.35 | | 0.40 | | | | | |
| а | а - | | 8° | | | | | |
| a1 | - | - | 7° | | | | | |
| All | Dimen | sions | in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.40 |
| C1 | 0.95 |
| G | 1.60 |
| Х | 0.55 |
| Y | 0.80 |
| Y1 | 3.20 |



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